

ABSTRACT

An integrated circuit includes multiple layers. A semiconductor-on-insulator (SOI) or silicon-on-insulator wafer can be used to house SMOS transistors. Two substrates or wafers can be bonded to form the multiple
5 layers. A strained silicon layer can be between a silicon germanium layer and a buried oxide layer. A hydrogen implant can provide a breaking interface to remove a silicon substrate from the silicon germanium layer.